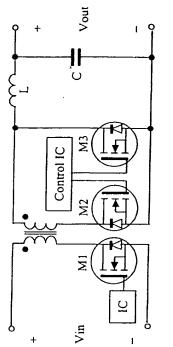
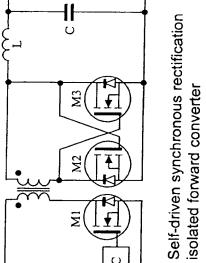
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IC-driven synchronous rectification isolated forward converter





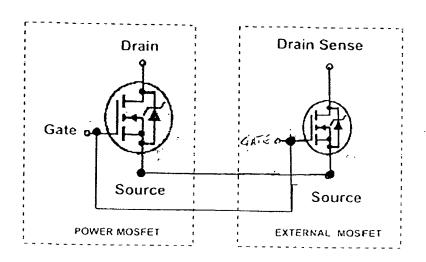
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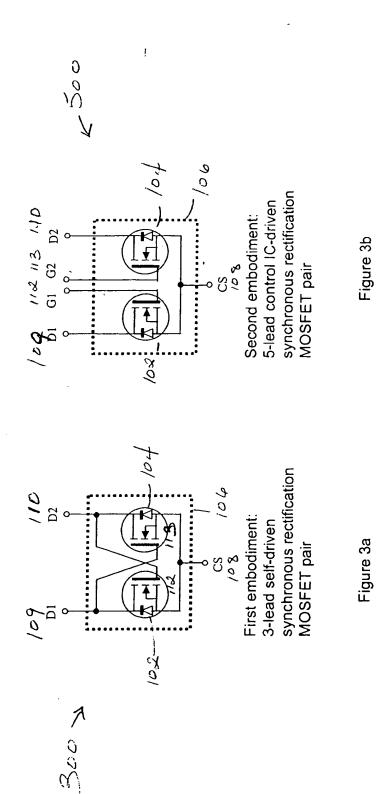


Figure 3

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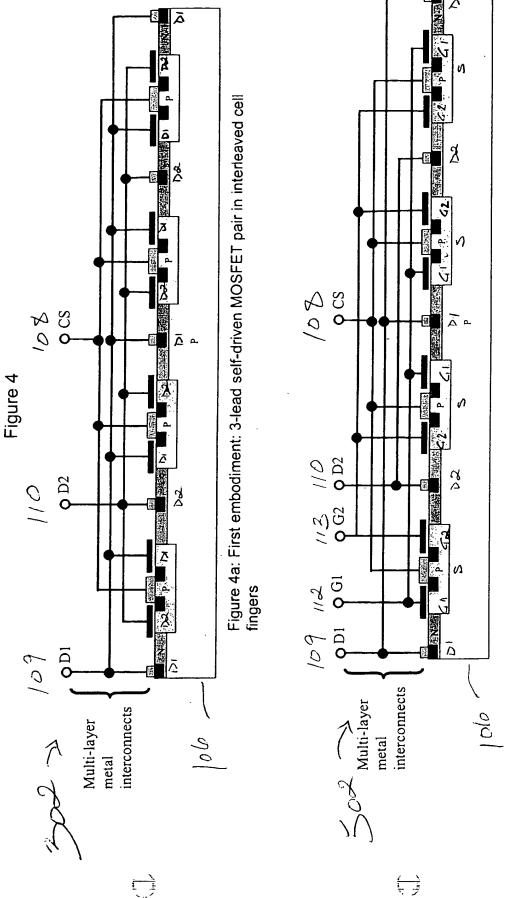


Figure 4b: Second embodiment: 5-lead external-driven MOSFET pair in interleaved cell fingers

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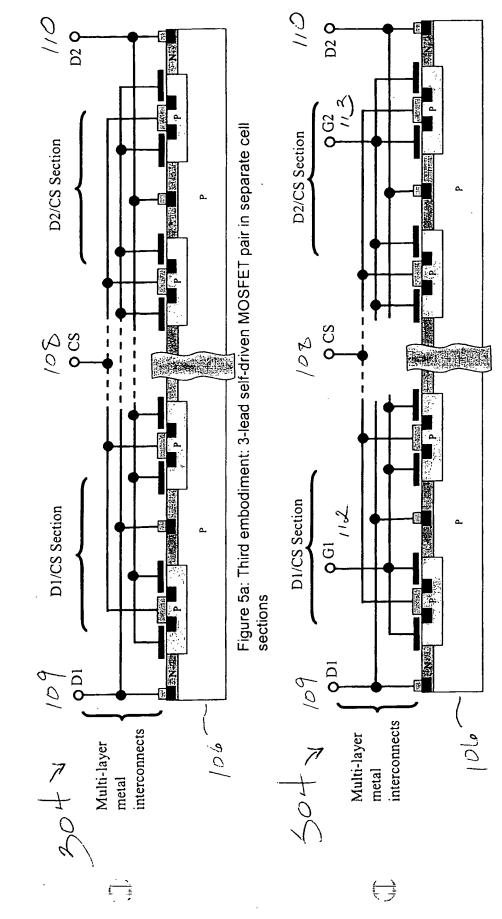


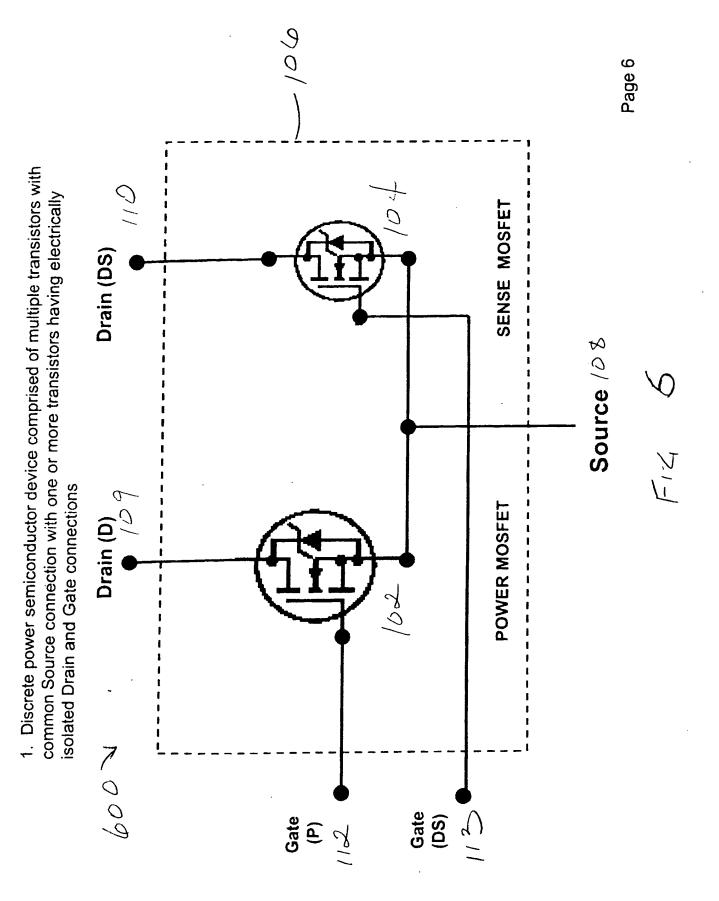
Figure 5

Figure 5b: Fourth embodiment: 5-lead external-driven MOSFET pair in separate cell sections

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1. Discrete power semiconductor device comprised of multiple transistors with common Source connection with one or more transistors having electrically isolated Drain and Gate connections

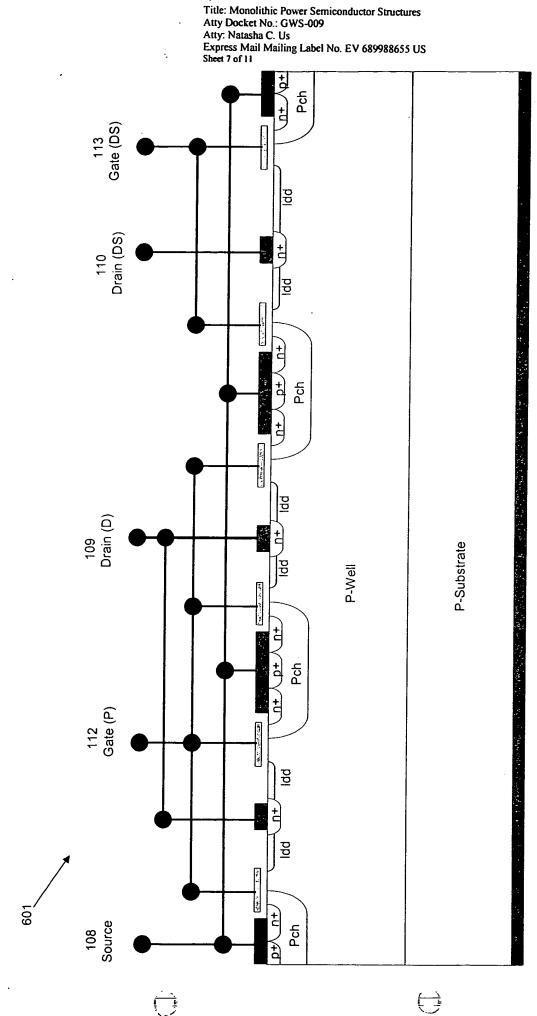


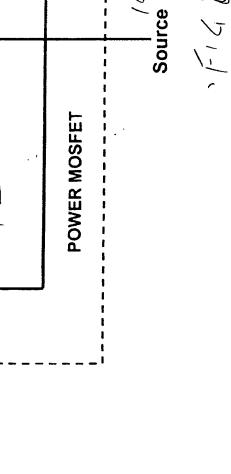
Figure 7

Cross-Sectional Diagram of a Power MOSFET With Integrated Drain Sense

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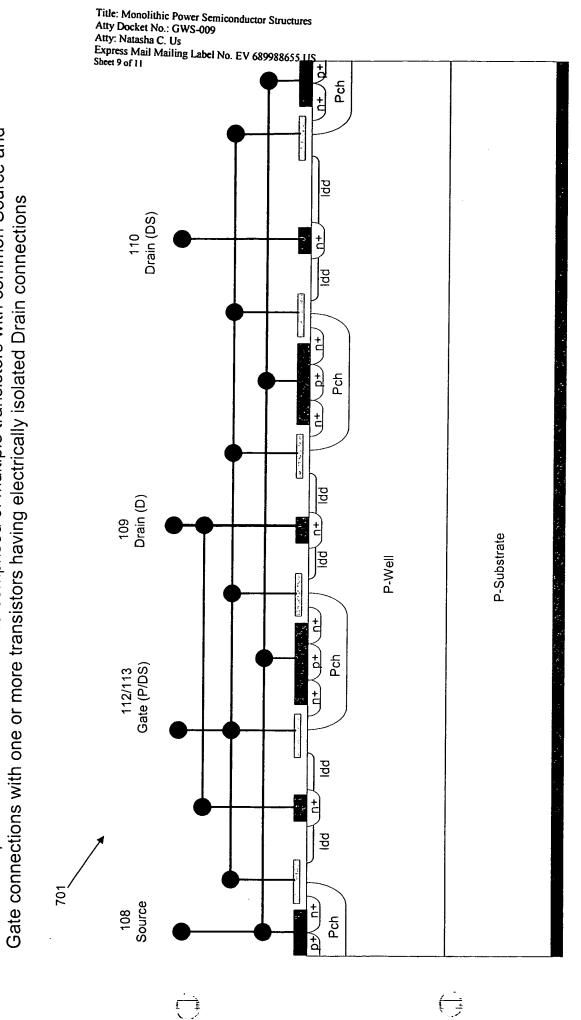
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2. Discrete power semiconductor device comprised of multiple transistors with common Source and Gate connections with one or more transistors having electrically isolated Drain connections SENSE MOSFET Drain (DS) Gate (P/DS)



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2. Discrete power semiconductor device comprised of multiple transistors with common Source and

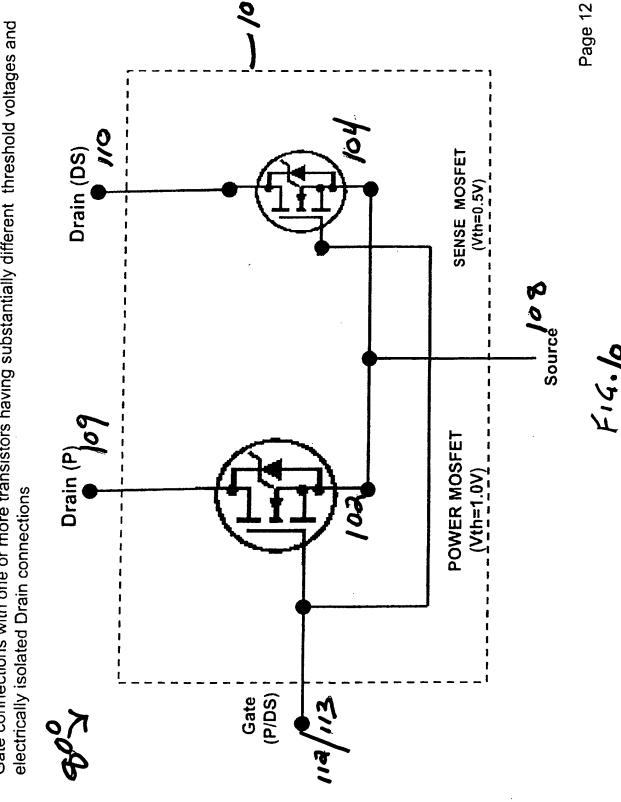


Cross-Sectional Diagram of a Power MOSFET With Integrated Drain Sense

Figure 9

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3. Discrete power semiconductor device comprised of multiple transistors with common Source and Gate connections with one or more transistors having substantially different threshold voltages and



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Cross-Sectional Diagram of a Power MOSFET With Integrated Drain Sense

Figure 11